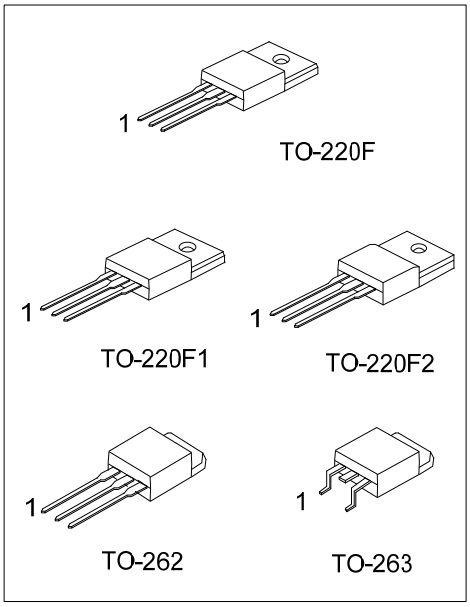
15N65-MT

Power MOSFET

15A, 650V N-CHANNEL POWER MOSFET



■ DESCRIPTION

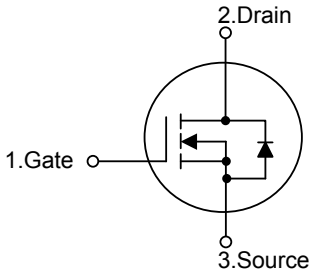
The UTC **15N65-MT** is an N-channel mode power MOSFET using UTC's advanced technology to provide customers with planar stripe and DMOS technology. This technology allows a minimum on-state resistance and superior switching performance. It also can withstand high energy pulse in the avalanche and commutation mode.

The UTC **15N65-MT** is generally applied in high efficiency switch mode power supplies.

■ FEATURES

* $R_{DS(ON)} \leq 0.55\ \Omega$ @ V_{GS}=10V, I_D=7.5A
* High Switching Speed

■ SYMBOL



■ ORDERING INFORMATION

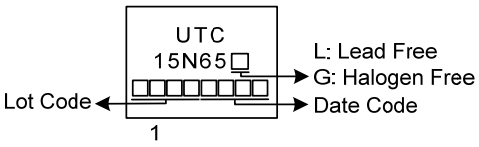
Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
15N65L-TF1-T	15N65G-TF1-T	TO-220F1	G	D	S	Tube
15N65L-TF2-T	15N65G-TF2-T	TO-220F2	G	D	S	Tube
15N65L-TF3-T	15N65G-TF3-T	TO-220F	G	D	S	Tube
15N65L-T2Q-T	15N65G-T2Q-T	TO-262	G	D	S	Tube
15N65L-TQ2-T	15N65G-TQ2-T	TO-263	G	D	S	Tube
15N65L-TQ2-R	15N65G-TQ2-R	TO-263	G	D	S	Tape Reel

Note: Pin Assignment: G: Gate D: Drain S: Source

15N65G-TF1-T
(1)Packing Type
(2)Package Type
(3)Green Package

(1) T: Tube, R: Tape Reel
(2) TF1: TO-220F1, TF2: TO-220F2, TF3: TO-220F, T2Q: TO-262, TQ2: TO-263
(3) G: Halogen Free and Lead Free, L: Lead Free

■ MARKING



■ ABSOLUTE MAXIMUM RATINGS (T_C=25°C, unless otherwise specified.) (Note 5)

PARAMETER			SYMBOL	RATINGS	UNIT
Drain to Source Voltage			V_{DSS}	650	V
Gate-Source Voltage			V_{GSS}	±30	V
Drain Current	Continuous	T_C=25°C	I_D	15	A
	Pulsed (Note 2)		I_{DM}	30	A
Avalanche Energy	Single Pulsed (Note 3)		E_{AS}	490	mJ
Peak Diode Recovery dv/dt (Note 4)			dv/dt	1.6	V/ns
Power Dissipation	TO-262/TO-263		P_D	240	W
	TO-220F/TO-220F1 TO-220F2			41	W
Junction Temperature			T_J	+150	°C
Storage Temperature			T_{STG}	-55 ~ +150	°C

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.
2. Repetitive Rating; Pulse width limited by maximum junction temperature.
3. L=10mH, I_{AS}=9.9A. V_{DD}=50V, R_G=25Ω, Starting T_J=25°C
4. I_{SD}≤15A, di/dt≤200A/μs, V_{DD}≤BV_{DSS}, Starting T_J=25°C
5. Drain current limited by maximum junction temperature.

■ THERMAL DATA

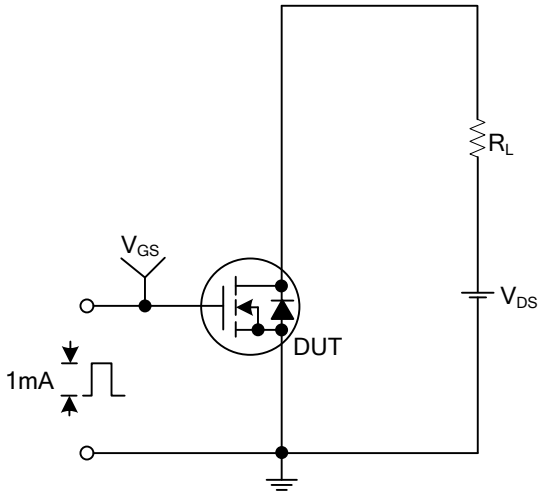
PARAMETER		SYMBOL	RATINGS	UNIT
Junction to Ambient		θ_{JA}	62.5	°C/W
Junction to Case	TO-262/TO-263	θ_{JC}	0.52	°C/W
	TO-220F/TO-220F1 TO-220F2		3	°C/W

■ ELECTRICAL CHARACTERISTICS

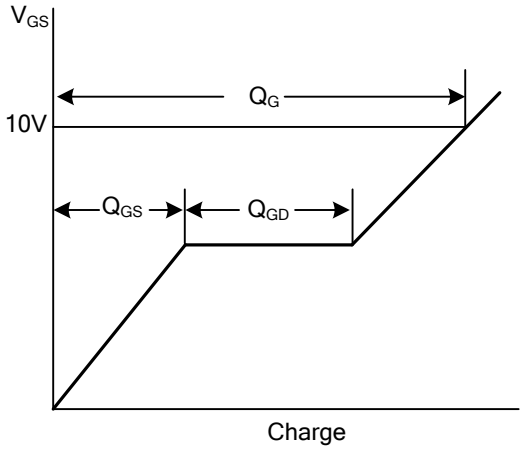
PARAMETER		SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS							
Drain-Source Breakdown Voltage		BV_{DSS}	I_D=250μA, V_{GS}=0V, T_J=25°C	650			V
Drain-Source Leakage Current		I_{DSS}	V_{DS}=650V, V_{GS}=0V			10	μA
Gate- Source Leakage Current	Forward	I_{GSS}	V_{GS}=+30V, V_{DS}=0V			+100	nA
	Reverse		V_{GS}=-30V , V_{DS}=0V			-100	nA
ON CHARACTERISTICS							
Gate Threshold Voltage		$V_{GS(TH)}$	V_{GS}=V_{DS}, I_D=250μA	2.0		4.0	V
Static Drain-Source On-State Resistance		$R_{DS(ON)}$	V_{GS}=10V, I_D=7.5A		0.48	0.55	Ω
DYNAMIC PARAMETERS							
Input Capacitance		C_{ISS}	V_{DS}=25V, V_{GS}=0V, f=1.0MHz		2230		pF
Output Capacitance		C_{OSS}			225		pF
Reverse Transfer Capacitance		C_{RSS}			14		pF
SWITCHING PARAMETERS							
Total Gate Charge		Q_G	V_{DS}=200V, V_{GS}=10V, I_D=15A (Note 1, 2)		45		nC
Gate to Source Charge		Q_{GS}			14		nC
Gate to Drain ("Miller") Charge		Q_{GD}			15		nC
Turn-ON Delay Time		$t_{D(ON)}$	V_{DS}=200V, I_D=15A, R_G=25Ω (Note 1, 2)		28		ns
Rise Time		t_R			24		ns
Turn-OFF Delay Time		$t_{D(OFF)}$			160		ns
Fall-Time		t_F			38		ns
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS							
Maximum Body-Diode Continuous Current		I_S				15	A
Maximum Body-Diode Pulsed Current		I_{SM}				30	A
Drain-Source Diode Forward Voltage		V_{SD}	I_S=15A, V_{GS}=0V			1.4	V
Body Diode Reverse Recovery Time		t_{rr}	I_S=15A, V_{GS}=0V, dI_F/dt=100A/μs		550		ns
Body Diode Reverse Recovery Charge		Q_{rr}			6.3		μC

Notes: 1. Pulse Test: Pulse width≤300μs; Duty Cycle≤2%
2. Essentially Independent of Operating Temperature Typical Characteristics

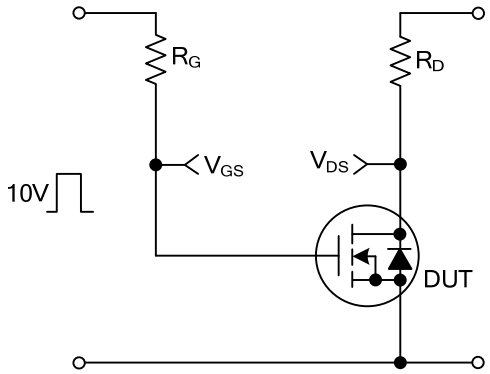
■ TEST CIRCUITS AND WAVEFORMS



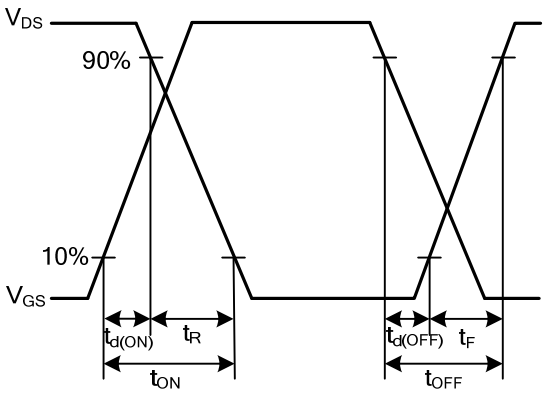
Gate Charge Test Circuit



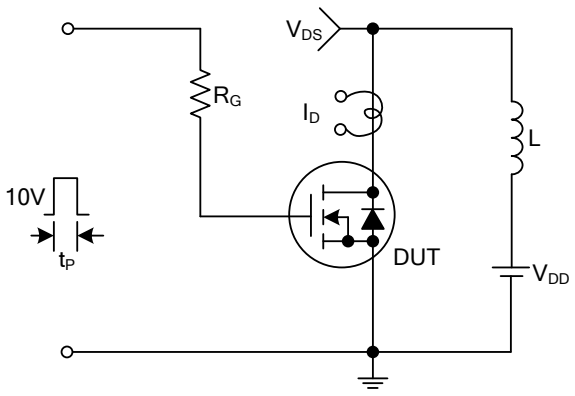
Gate Charge Waveforms



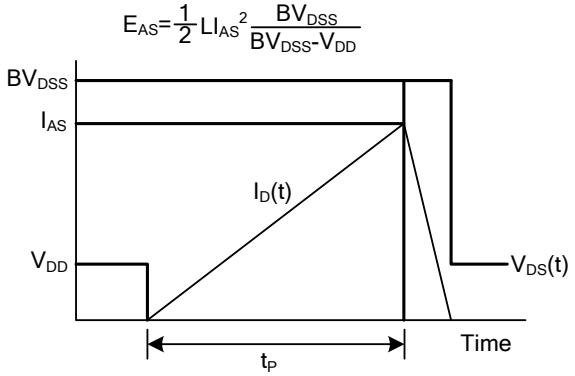
Resistive Switching Test Circuit



Resistive Switching Waveforms



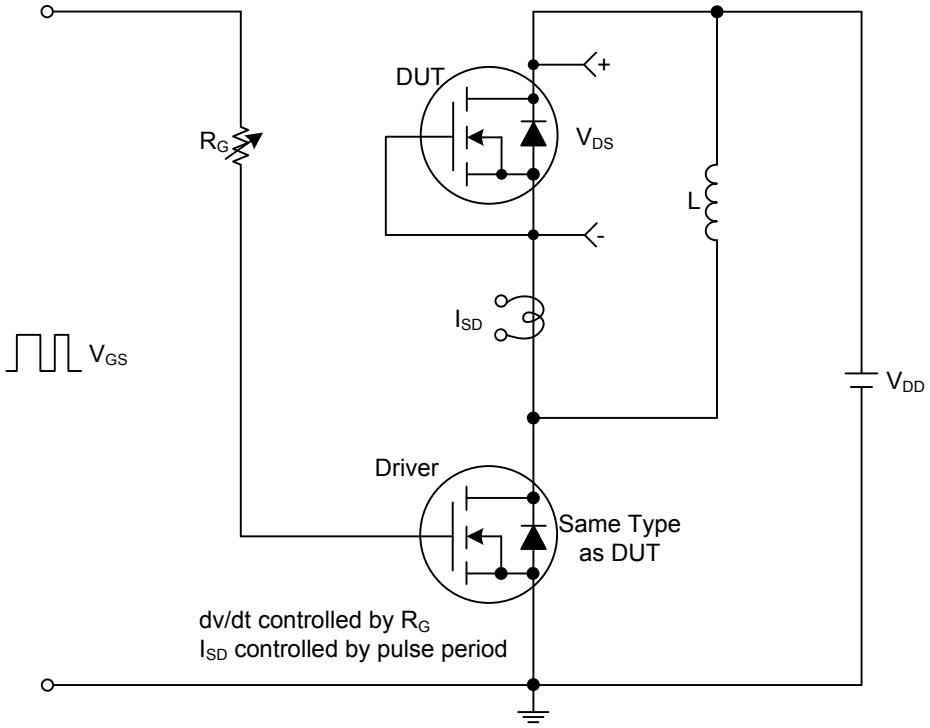
Unclamped Inductive Switching Test Circuit

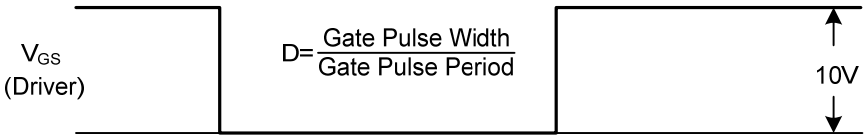


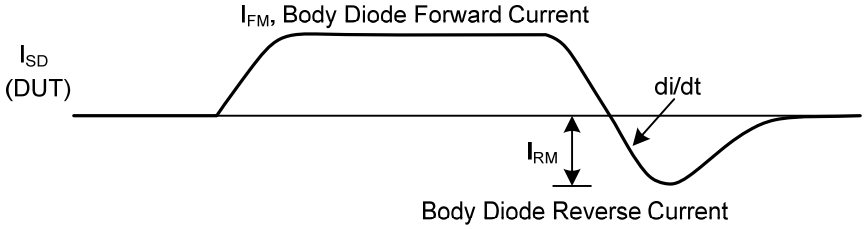
Unclamped Inductive Switching Waveforms

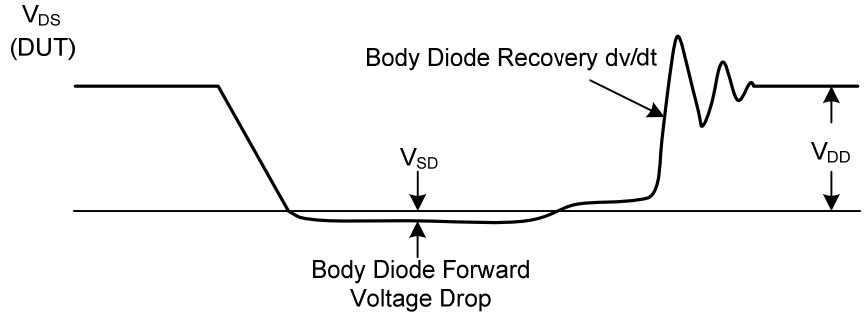
■ TEST CIRCUITS AND WAVEFORMS

Peak Diode Recovery dv/dt Test Circuit & Waveforms



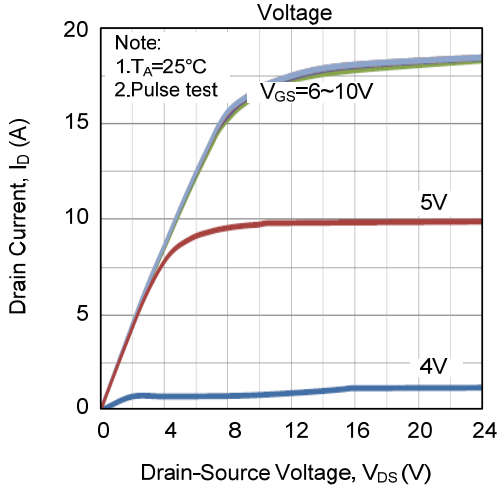




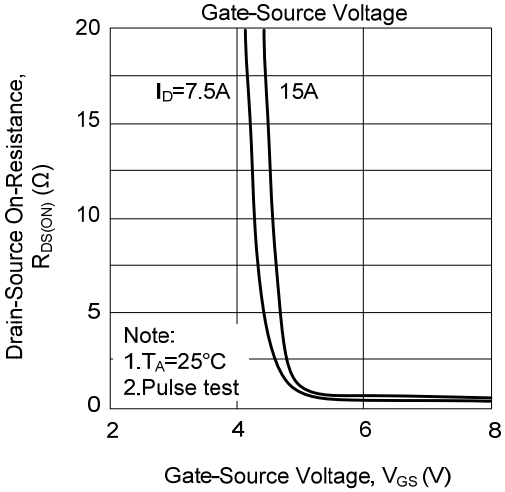


■ TYPICAL CHARACTERISTICS

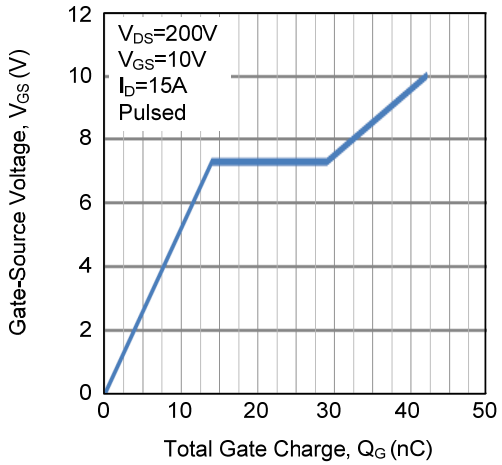
Drain Current vs. Drain-Source Voltage



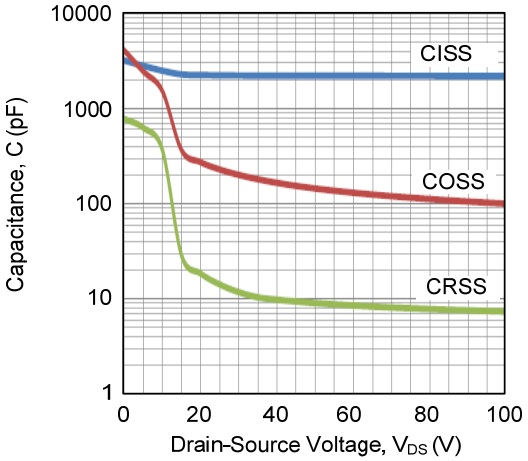
Drain-Source On-Resistance vs. Gate-Source Voltage



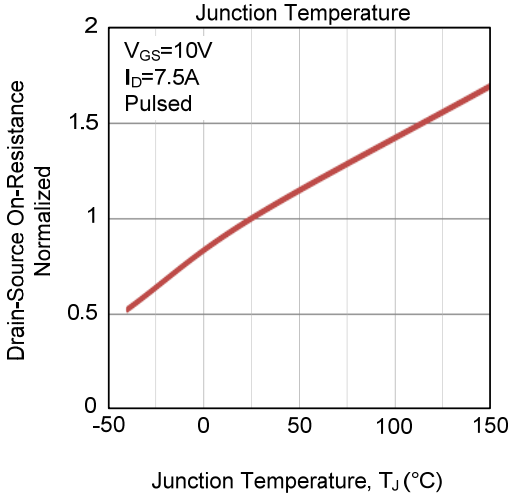
Gate Charge Characteristics



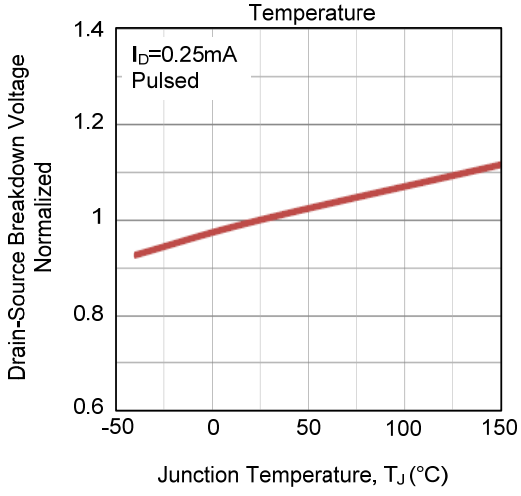
Capacitance Characteristics



Drain-Source On-Resistance vs. Junction Temperature

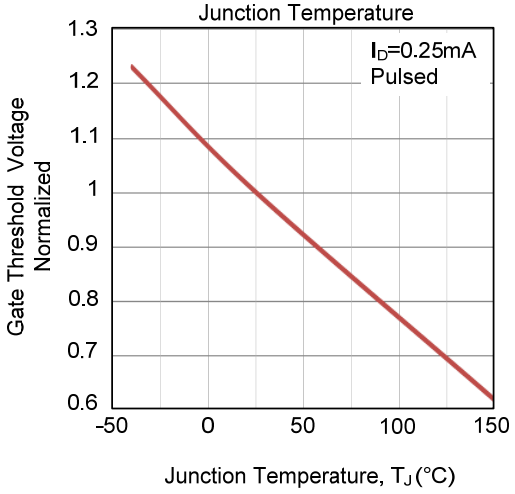


Breakdown Voltage vs. Junction Temperature

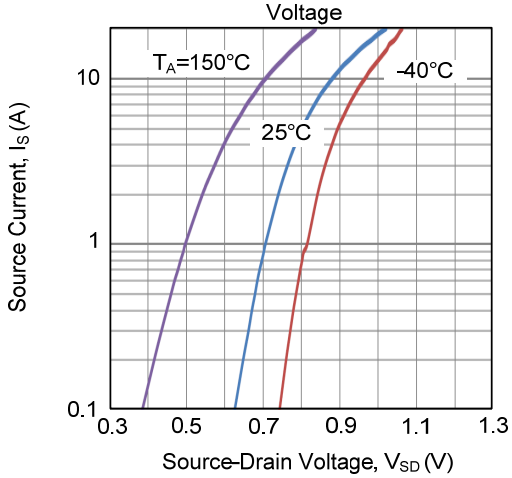


■ TYPICAL CHARACTERISTICS (Cont.)

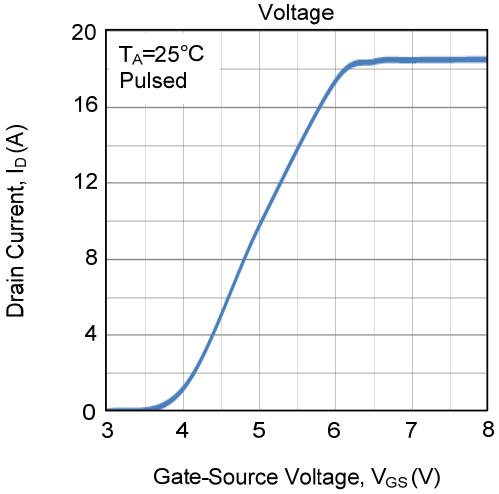
Gate Threshold Voltage vs. Junction Temperature



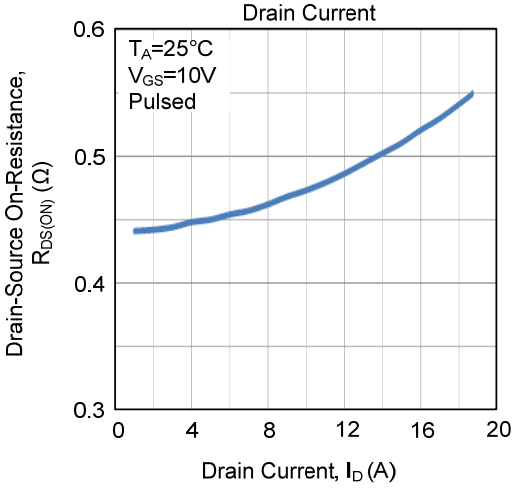
Source Current vs. Source-Drain Voltage



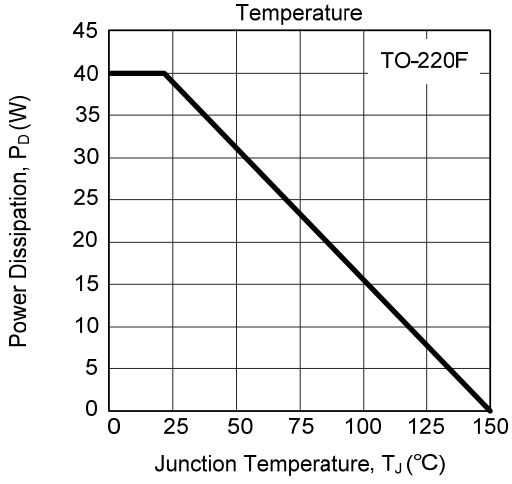
Drain Current vs. Gate-Source Voltage



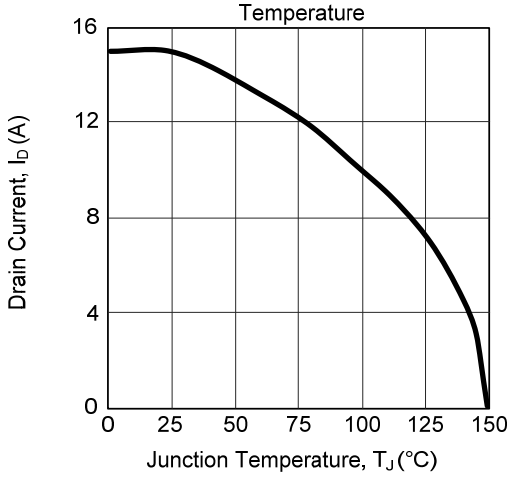
Drain-Source On-Resistance vs. Drain Current



Power Dissipation vs. Junction Temperature



Drain Current vs. Junction Temperature



■ TYPICAL CHARACTERISTICS (Cont.)